STLD200N4F6AG

Automotive-grade N-channel 40 V, 1.27 mΩ typ., 120 A STripFET™ F6 Power MOSFET in a PowerFLAT™ 5x6 DSC

Datasheet - production data

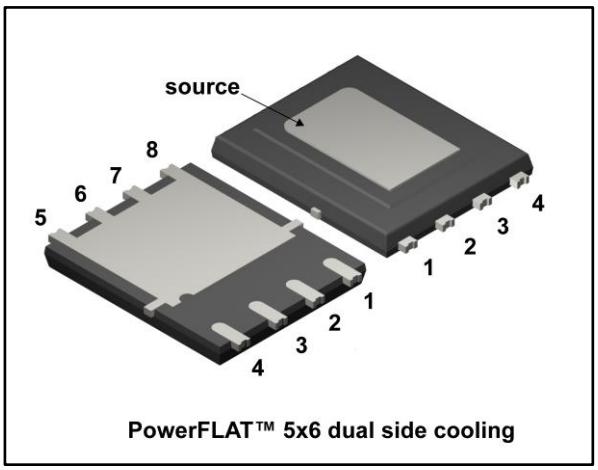
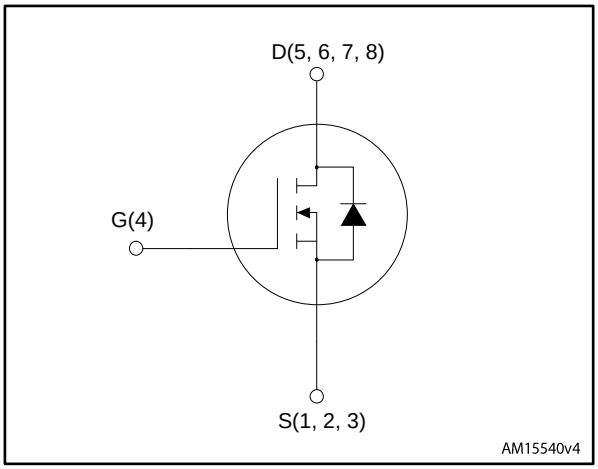


Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STLD200N4F6AG	40 V	1.50 mΩ	120 A

- AEC-Q101 qualified
- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss
- Wettable flank package

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the STripFET™ F6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low $R_{DS(on)}$ in all packages.

Table 1: Device summary

Order code	Marking	Package	Packaging
STLD200N4F6AG	200	PowerFLAT™ 5x6 dual side cooling	Tape and reel

Contents

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	40	V
V_{GS}	Gate-source voltage	±20	V
I_D (1)(2)	Drain current (continuous) at T_C = 25 °C	120	A
I_D (1)(2)	Drain current (continuous) at T_C = 100 °C	120	A
I_{DM} (2)(3)	Drain current (pulsed)	480	A
P_{TOT} (2)	Total dissipation at T_C = 25 °C	158	W
T_J	Operating junction temperature range	-55 to 175	°C
T_{stg}	Storage temperature range		

Notes:

(1)Limited by package

(2)The value is rated according to $R_{thj\text{-case bottom side}}$.

(3)Pulse width limited by safe operating area

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-c top side}}$	Thermal resistance junction-case top side	2.90	°C/W
$R_{thj\text{-c bottom side}}$	Thermal resistance junction-case bottom side	0.95	
$R_{thj\text{-pcb}}$ (1)	Thermal resistance junction-pcb	31.3	

Notes:

(1)When mounted on 1 inch² 2 Oz. Cu board, t ≤ 10 s

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AV}	Avalanche current, repetitive or not repetitive (pulse width limited by maximum junction temperature)	90	A
E_{AS}	Single pulse avalanche energy (T_j = 25 °C, I_C = I_{AV}, V_{DD} = 16 V)	400	mJ

2 Electrical characteristics

(T_C= 25 °C unless otherwise specified)

Table 5: On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	40			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 16 V			1	µA
		V_{GS} = 0 V, V_{DS} = 16 V, Tj = 125 °C (1)			10	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2.5		3.5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 75 A		1.27	1.50	mΩ
		V_{GS} = 6.5 V, I_D = 75 A		1.48	2.00	

Notes:

(1)Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS}= 10 V, f = 1 MHz, V_{GS} = 0 V	-	10700	-	pF
C_{oss}	Output capacitance		-	1530	-	pF
C_{rss}	Reverse transfer capacitance		-	1100	-	pF
Q_g	Total gate charge	V_{DD} = 32 V, I_D = 90 A, V_{GS} = 0 to 10 V (see *Figure 14: "Test circuit for gate charge behavior"*)	-	172	-	nC
Q_{gs}	Gate-source charge		-	56	-	nC
Q_{gd}	Gate-drain charge		-	48	-	nC

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 30 V, I_D = 75 A R_G = 30 Ω, V_{GS} = 10 V (see *Figure 13: "Test circuit for resistive load switching times"* and *Figure 18: "Switching time waveform"*)	-	150	-	ns
t_r	Rise time		-	440	-	ns
$t_{d(off)}$	Turn-off-delay time		-	600	-	ns
t_f	Fall time		-	410	-	ns

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} (1)	Source-drain current		-		120	A
I_{SDM} (1)(2)	Source-drain current (pulsed)		-		480	A
V_{SD} (3)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 90 A	-		1.2	V
t_{rr}	Reverse recovery time	I_{SD} = 90 A, di/dt = 100 A/µs, V_{DD} = 20 V (see *Figure 15: "Test circuit for inductive load switching and diode recovery times"*)	-	40		ns
Q_{rr}	Reverse recovery charge		-	53		nC
I_{RRM}	Reverse recovery current		-	2.5		A

Notes:

(1)Limited by package.

(2)Pulse width is limited by safe operating area.

(3)Pulse test: pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

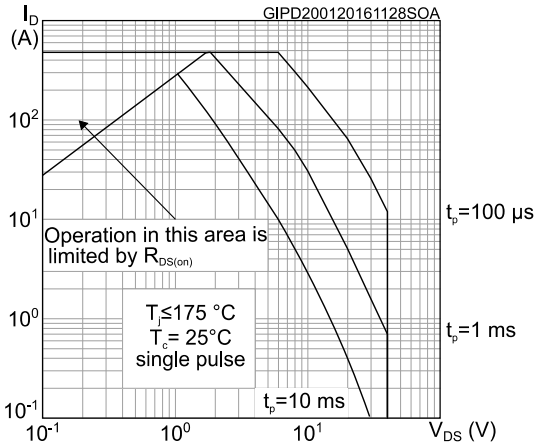


Figure 3: Thermal impedance

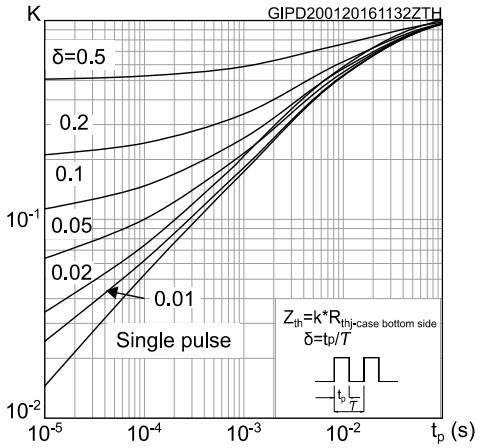


Figure 4: Output characteristics

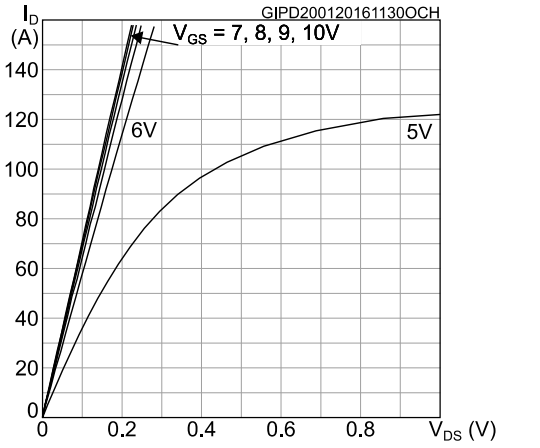


Figure 5: Transfer characteristics

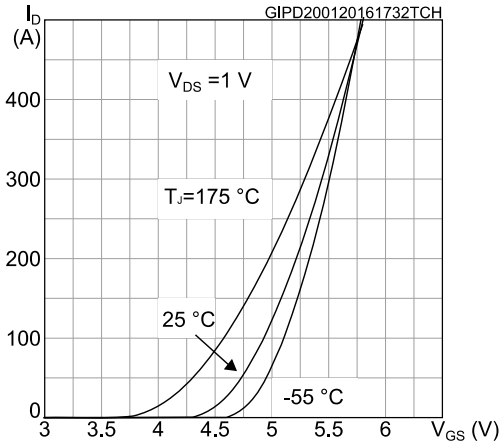


Figure 6: Gate charge vs gate-source voltage

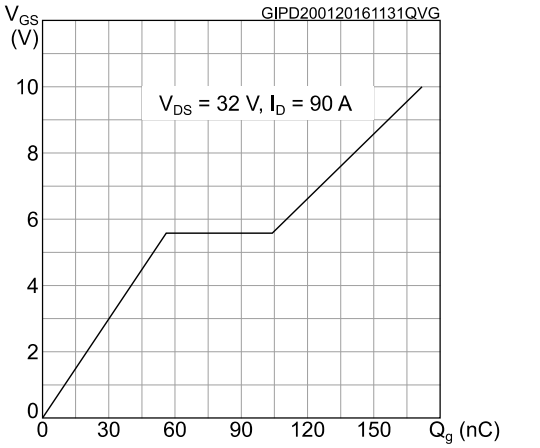


Figure 7: Static drain-source on-resistance

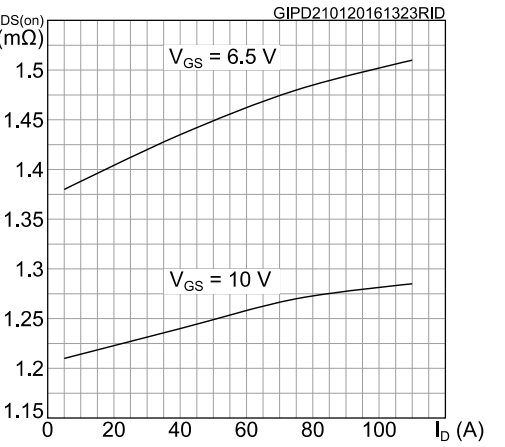


Figure 8: Capacitance variations

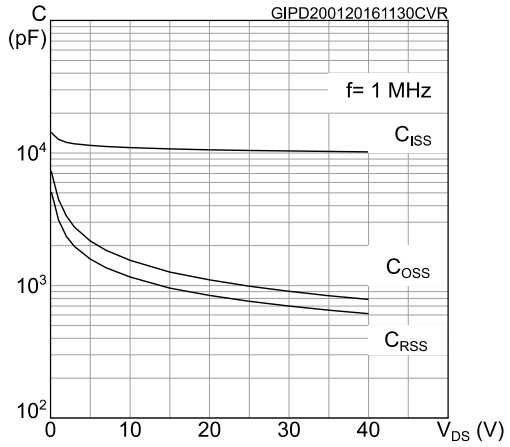


Figure 9: Normalized gate threshold voltage vs temperature

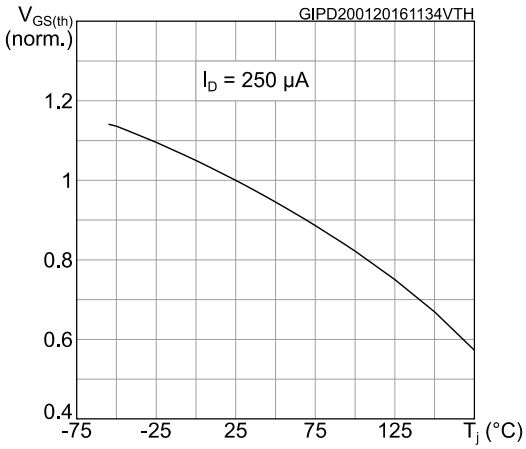


Figure 10: Normalized on-resistance vs temperature

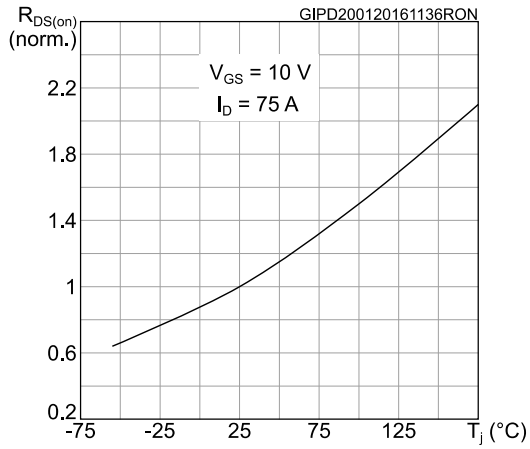


Figure 11: Normalized $V_{(BR)DSS}$ vs temperature

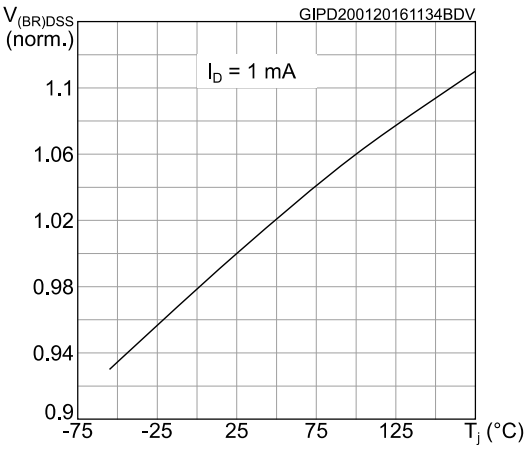
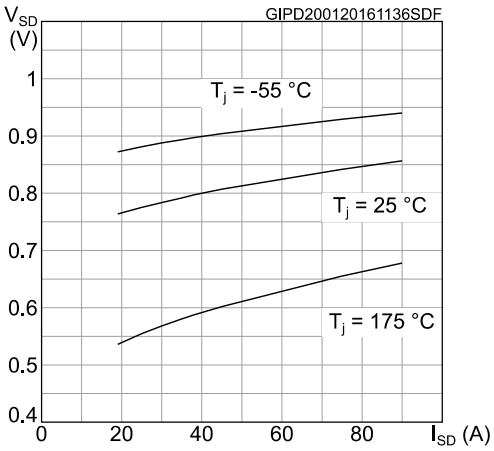


Figure 12: Source-drain diode forward characteristics



3 Test circuits

Figure 13: Test circuit for resistive load switching times

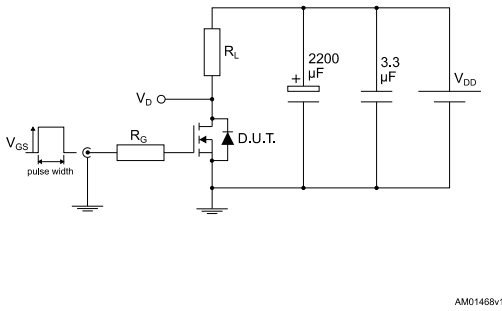


Figure 14: Test circuit for gate charge behavior

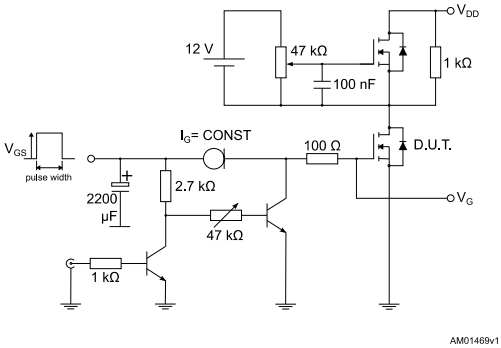


Figure 15: Test circuit for inductive load switching and diode recovery times

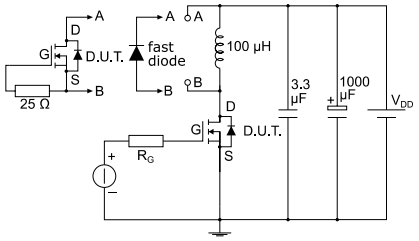


Figure 16: Unclamped inductive load test circuit

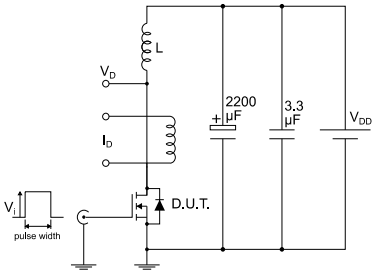


Figure 17: Unclamped inductive waveform

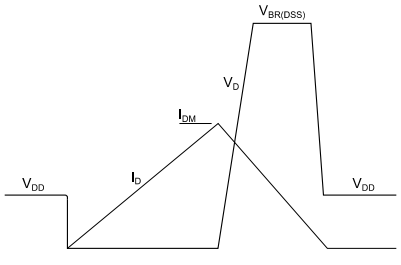
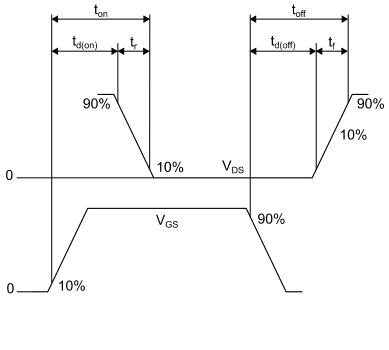


Figure 18: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 PowerFLAT™ 5x6 dual side cooling package information

Figure 19: PowerFLAT™ 5x6 dual side cooling package outline

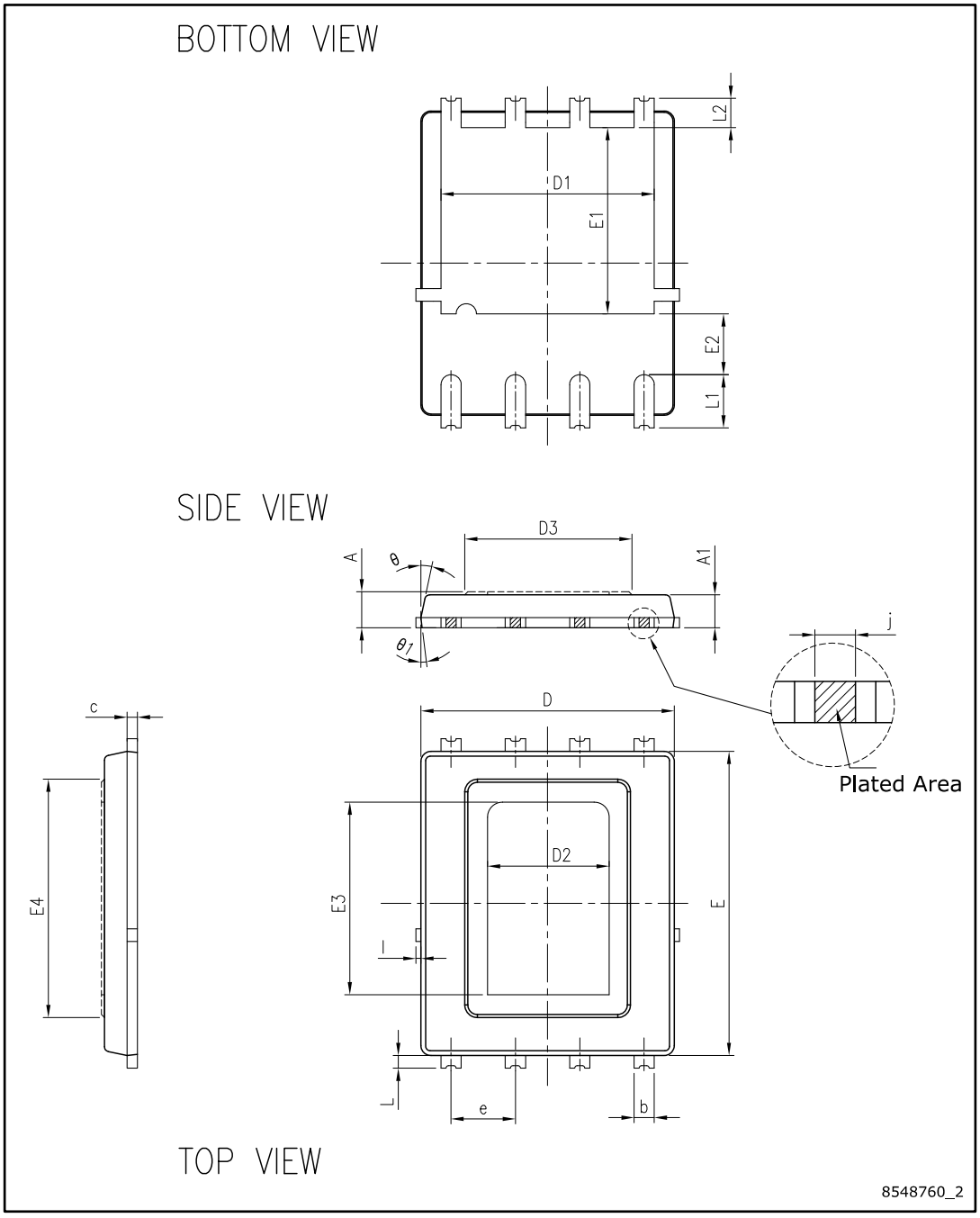
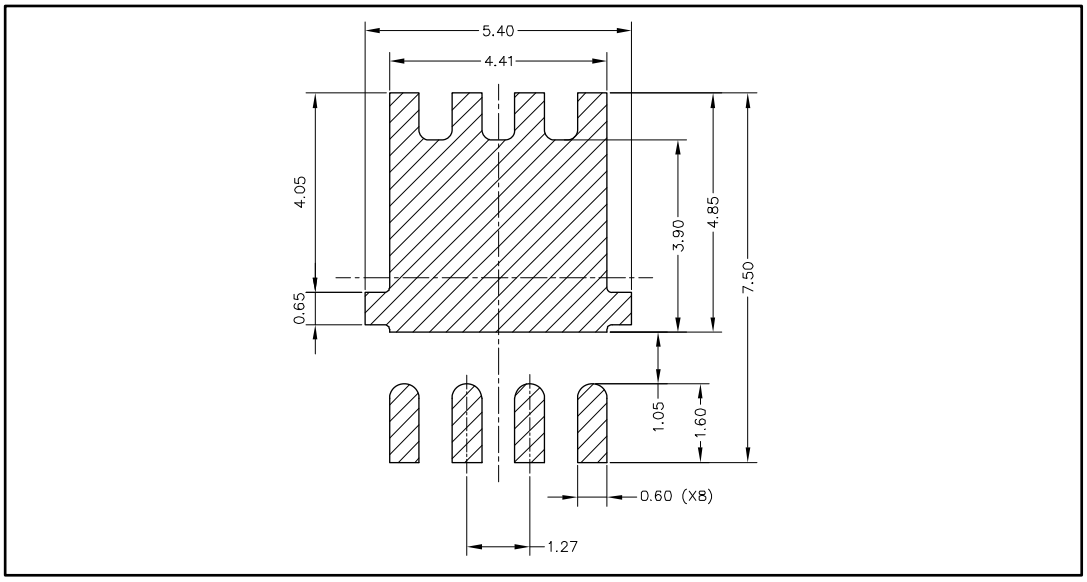


Table 9: PowerFLAT™ 5x6 dual side cooling mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.66	0.71	0.76
A1	0.60		0.75
b	0.33	0.43	0.53
c	0.15	0.203	0.30
D		5.00 BSC	
D1	4.06	4.21	4.36
D2		2.40 BSC	
D3	2.80	3.30	3.80
E		6.00 BSC	
E1	3.525	3.675	3.825
E2	1.05	1.20	1.35
E3		3.80 BSC	
E4	4.20	4.70	5.20
e		1.27 BSC	
I			0.15
L	0.15	0.25	0.35
L1	0.925	1.05	1.175
L2	0.45	0.575	0.70
ϑ		12° BSC	
ϑ1		7° BSC	
j		0.20 BSC	

Figure 20: PowerFLAT™ 5x6 dual side cooling recommended footprint (dimensions are in mm)



4.2 PowerFLAT™ 5x6 dual side cooling packing information

Figure 21: PowerFLAT™ 5x6 dual side cooling tape (dimensions are in mm)

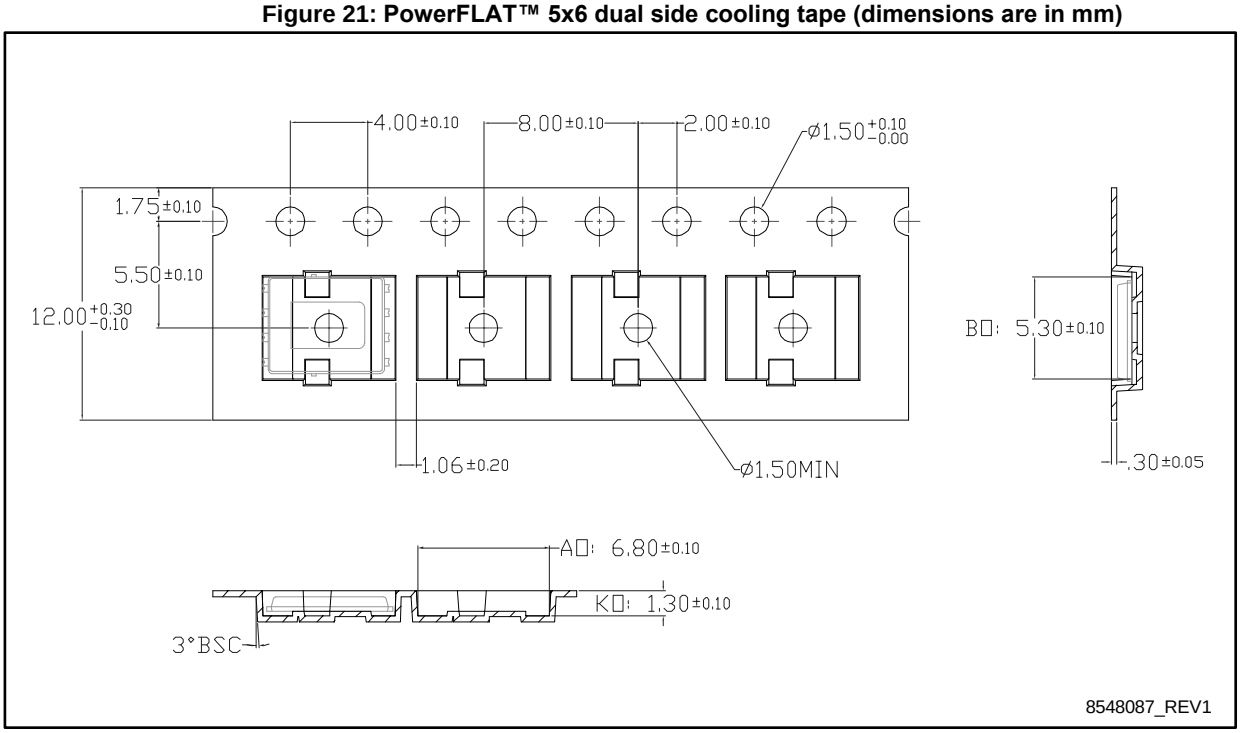
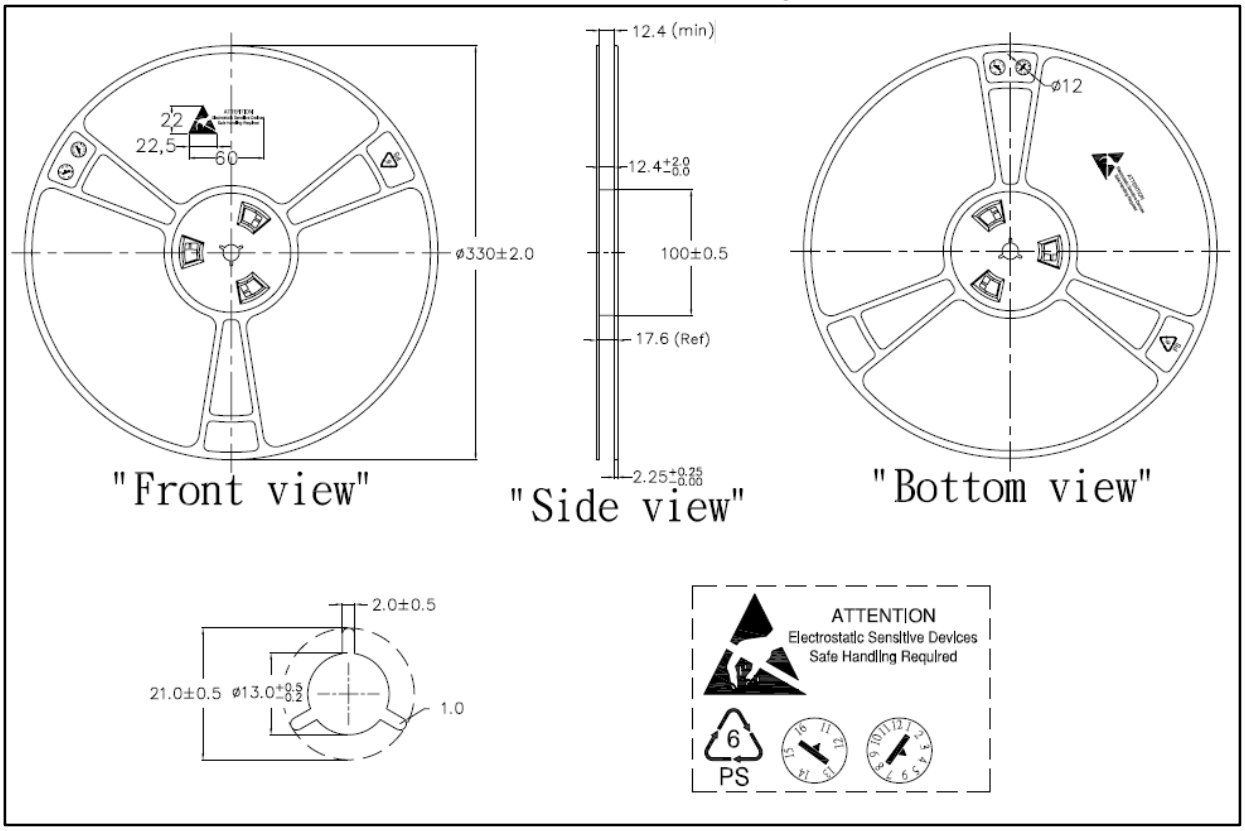


Figure 22: PowerFLAT™ 5x6 dual side cooling reel (dimensions are in mm)



5 Revision history

Table 10: Document revision history

Date	Revision	Changes
19-Jan-2016	1	First release
07-Feb-2017	2	Document status promoted from preliminary to production data. Updated *Table 3: "Thermal data"* and *Table 5: "On/off states"*. Minor text changes
23-Feb-2017	3	Updated features on cover page. Updated *Table 5: "On/off states"* and *Figure 9: "Normalized gate threshold voltage vs temperature"* Minor text changes
04-Apr-2017	4	Updated test conditions in *Table 7: "Switching times"*.
12-Jul-2017	5	Added *Section 4.2: "PowerFLAT™ 5x6 dual side cooling packing information"*.

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